L	Hits	Search Text	DB	Time stamp
Number				
2	1430	(gate adj electrode) and (drain adj	USPAT;	2004/10/27
		electrode) and (source adj electrode) and	US-PGPUB	18:02
		(light near2 emitting)		
3	581	((gate adj electrode) and (drain adj	USPAT;	2004/10/27
		electrode) and (source adj electrode) and	US-PGPUB	17:51
		(light near2 emitting)) and hole and		-30
		(semiconductor near2 (film or layer))		
4	215	1,1,9	USPAT;	2004/10/27
		electrode) and (source adj electrode) and	US-PGPUB	17:51
		(light near2 emitting)) and hole and		
`		(semiconductor near2 (film or layer)))	· .	
		and passivation	·	
5	106	((((gate adj electrode) and (drain adj	USPAT;	2004/10/27
		electrode) and (source adj electrode) and	US-PGPUB	17:51
		(light near2 emitting)) and hole and		
		(semiconductor near2 (film or layer)))		
		and passivation) and @ad<20020711		
6	52	, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	2004/10/27
		electrode) and (source adj electrode) and	DERWENT;	18:02
		(light near2 emitting)	IBM TDB	ll